

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims, including those in the First Preliminary Amendment, in the application:

Listing of Claims:

Claim 1 (currently amended): ~~High purity hafnium and a target and thin film formed from said high purity hafnium~~ having a purity of 4N or higher excluding zirconium and gas components, ~~and an oxygen content of 40wtppm or less, a sulfur content of 10wtppm or less, a phosphorus content of 10wtppm or less, and a zirconium content of 0.1wt% or less.~~

Claim 2 (currently amended): ~~High purity hafnium and a~~ A sputtering target and or thin film, comprising a sputtering target or thin film formed from said ~~of~~ high purity hafnium having a purity of 4N or higher excluding zirconium and gas components, an oxygen content of 40wtppm or less, and in which the content of a sulfur and content of 10wtppm or less, a phosphorus is respectively content of 10wtppm or less, and a zirconium content of 0.1wt% or less.

Claims 3-4 (canceled).

Claim 5 (currently amended): A method of manufacturing ~~method of~~ high purity hafnium, comprising the steps of:

~~wherein~~ subjecting a hafnium ~~sponge~~ raw material ~~is subject~~ to solvent extraction and thereafter dissolved dissolving the raw material,

~~and the obtained~~ obtaining a hafnium ingot is further subject from the raw material after
said solvent extraction and subjecting the ingot to deoxidation with molten salt,
and
after said deoxidation, subjecting the ingot to electron beam melting.

Claim 6 (canceled).